

# Jan Kopaczek

## List of Publications by Year in descending order

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19  
papers

464  
citations

687363

13  
h-index

794594

19  
g-index

19  
all docs

19  
docs citations

19  
times ranked

516  
citing authors

#	ARTICLE	IF	CITATIONS
1	Photoreflectance studies of temperature and hydrostatic pressure dependencies of direct optical transitions in BGaAs alloys grown on GaP. <i>Journal Physics D: Applied Physics</i> , 2022, 55, 015107.	2.8	3
2	Temperature Dependence of the Indirect Gap and the Direct Optical Transitions at the High-Symmetry Point of the Brillouin Zone and Band Nesting in MoS <sub>2</sub> , MoSe <sub>2</sub> , MoTe <sub>2</sub> , WS <sub>2</sub> , and WSe <sub>2</sub> Crystals. <i>Journal of Physical Chemistry C</i> , 2022, 126, 5665-5674.	3.1	16
3	Strong Substrate Strain Effects in Multilayered WS <sub>2</sub> Revealed by High-Pressure Optical Measurements. <i>ACS Applied Materials &amp; Interfaces</i> , 2022, , .	8.0	8
4	Experimental and Theoretical Studies of the Electronic Band Structure of Bulk and Atomically Thin Mo <sub>1-x</sub> W <sub>x</sub> Se <sub>2</sub> Alloys. <i>ACS Omega</i> , 2021, 6, 19893-19900.	3.5	9
5	Optical properties and dynamics of excitons in Ga(Sb, Bi)/GaSb quantum wells: evidence for a regular alloy behavior. <i>Semiconductor Science and Technology</i> , 2020, 35, 025024.	2.0	3
6	Hidden spin-polarized bands in semiconducting 2H-MoTe <sub>2</sub> . <i>Materials Research Letters</i> , 2020, 8, 75-81.	8.7	17
7	Type I GaSb <sub>1-x</sub> Bi <sub>x</sub> /GaSb quantum wells dedicated for mid infrared laser applications: Photoreflectance studies of bandgap alignment. <i>Journal of Applied Physics</i> , 2019, 125, .	2.5	16
8	Direct and indirect optical transitions in bulk and atomically thin MoS <sub>2</sub> studied by photoreflectance and photoacoustic spectroscopy. <i>Journal of Applied Physics</i> , 2019, 125, .	2.5	17
9	Optical spectroscopy studies of atom intermixing in the core versus growth temperature of the claddings in MOCVD-grown quantum cascade lasers. <i>Journal of Physics Communications</i> , 2019, 3, 125007.	1.2	1
10	Bowing of the band gap and spin-orbit splitting energy in BGaAs. <i>Materials Research Express</i> , 2019, 6, 125913.	1.6	8
11	Structural and optical properties of GaSbBi/GaSb quantum wells [Invited]. <i>Optical Materials Express</i> , 2018, 8, 893.	3.0	15
12	Direct optical transitions at K- and H-point of Brillouin zone in bulk MoS <sub>2</sub> , MoSe <sub>2</sub> , WS <sub>2</sub> , and WSe <sub>2</sub> . <i>Journal of Applied Physics</i> , 2016, 119, .	2.5	46
13	Pressure coefficients for direct optical transitions in MoS <sub>2</sub> , MoSe <sub>2</sub> , WS <sub>2</sub> , and WSe <sub>2</sub> crystals and semiconductor to metal transitions. <i>Scientific Reports</i> , 2016, 6, 26663.	3.3	56
14	Optical properties of GaAsBi/GaAs quantum wells: Photoreflectance, photoluminescence and time-resolved photoluminescence study. <i>Semiconductor Science and Technology</i> , 2015, 30, 094005.	2.0	30
15	Theoretical and experimental studies of electronic band structure for GaSb <sub>1-x</sub> Bi <sub>x</sub> in the dilute Bi regime. <i>Journal Physics D: Applied Physics</i> , 2014, 47, 355107.	2.8	50
16	High Bi content GaSbBi alloys. <i>Journal of Applied Physics</i> , 2014, 116, .	2.5	70
17	Temperature dependence of the band gap of GaSb <sub>1-x</sub> Bi <sub>x</sub> alloys with $\Delta E_g \approx 0.042$ determined by photoreflectance. <i>Applied Physics Letters</i> , 2013, 103, .	3.3	46
18	Unusual broadening of E <sub>0</sub> and E <sub>0</sub> + $\hat{\Gamma}$ SO transitions in GaAsBi studied by electromodulation spectroscopy. <i>Journal of Applied Physics</i> , 2012, 111, 066103.	2.5	20

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19	Contactless electroreflectance study of E0 and E0+â€‰%+â€‰%Î”SO transitions in In0.53Ga0.47BixAs1âˆ²x alloys. Applied Physics Letters, 2011, 99, 251906.	3.3	33